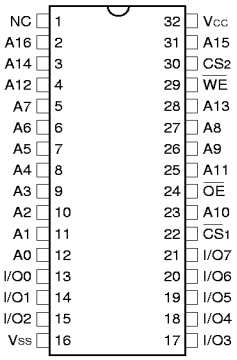
128Kx8 SRAM *PRELIMINARY**

EVOLUTIONARY PINOUT
TOP VIEW



PIN DESCRIPTION

A0-16	Address Inputs
I/O0-7	Data Input/Output
$\overline{CS}_1$, CS_2	Chip Selects
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
VCC	+5.0V Power
VSS	Ground

PLASTIC PLUS™ FEATURES

- Access Times: 17, 20nS Industrial Temp Range
  20nS Military Temp Range
- Standard Commercial Off-The-Shelf (COTS) Memory Devices for Extended Temperature Range
- JEDEC Standard 32 lead Plastic 0.400" SOJ Package
- Electrical and Speed Characteristics for:
  - Military Temperature (-55°C to +125°C)
  - Industrial Temperature (-40°C to +85°C)
- Burn-in and Temperature Cycling Available
- Organized as 128K x 8
- Pinout:
  - Evolutionary, Corner Power/Ground Pin
- 5 Volt Power Supply
- Low Power CMOS
- 2V Data Retention for Battery Backup Operation
- Low Data Retention Current at Vcc = 3V Industrial Temperature Range: L-version
- Dual Chip Select
- Reliability Test Data Available:
  - High Temperature Operating Life
  - High Temperature Storage
  - Pressure Cooker Test
  - Wet High Temperature Operating Life
  - Thermal Shock
  - Temperature Cycling

* *This data sheet describes a product under development, not fully characterized, and is subject to change without notice.*

PLASTIC *PLUS* SRAM

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature (Mil.)	T_A	-55	+125	°C
Operating Temperature (Ind.)	T_A	-40	+85	°C
Storage Temperature	T_{STG}	-65	+150	°C
Signal Voltage Relative to GND	V_G	-0.5	V_{CC} + 0.5	V
Supply Voltage	V_{CC}	-0.5	7.0	V

TRUTH TABLE

$\overline{CS1}$	CS2	$\overline{OE}$	$\overline{WE}$	Mode	Data I/O	Power
H	X	X	X	Standby	High Z	Standby
X	L	X	X	Standby	High Z	Standby
L	H	L	H	Read	Data Out	Active
L	H	H	H	Out Disable	High Z	Active
L	H	X	L	Write	High Z	Active

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	4.5	5.5	V
Input High Voltage	V_{IH}	2.2	V_{CC} + 0.5	V
Input Low Voltage	V_{IL}	-0.3	+0.8	V
Operating Temperature (Mil.)	T_A	-55	+125	°C
Operating Temperature (Ind.)	T_A	-40	+85	°C

CAPACITANCE

(T_A = +25°C)

Parameter	Symbol	Condition	Max	Unit
Input capacitance	C_{IN}	V_{IN} = 0V, f = 1.0MHz	6	pF
Output capacitance	C_{OUT}	V_{OUT} = 0V, f = 1.0MHz	8	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Symbol	Conditions	Min	Max	Units
Input Leakage Current	I_{LI}	V_{CC} = 5.5, V_{IN} = GND to V_{CC}		10	µA
Output Leakage Current	I_{LO}	$\overline{CS}$ = V_{IH}, $\overline{OE}$ = V_{IH}, V_{OUT} = GND to V_{CC}		10	µA
Operating Supply Current	I_{CC}	$\overline{CS}$ = V_{IL}, $\overline{OE}$ = V_{IH}, f = 5MHz, V_{CC} = 5.5		110	mA
Standby Current	I_{SB}	$\overline{CS}$ = V_{IH}, $\overline{OE}$ = V_{IH}, f = 5MHz, V_{CC} = 5.5		5	mA
Output Low Voltage	V_{OL}	I_{OL} = 8mA, V_{CC} = 4.5		0.4	V
Output High Voltage	V_{OH}	I_{OH} = -4mA, V_{CC} = 4.5	2.4		V

NOTE: DC test conditions: V_{IL} = 0.3V, V_{IH} = V_{CC} -0.3V

DATA RETENTION CHARACTERISTICS

(T_A = -55°C to +125°C)

Parameter	Symbol	Conditions	Min	Max	Units
Data Retention Supply Voltage	V_{DR}	$\overline{CS_1}$ Controlled: $\overline{CS_1} \geq V_{CC}$ - 0.2V, $CS_2 \geq V_{CC}$ - 0.2V CS_2 Controlled: $CS_2 \leq$ 0.2V	2.0	5.5	V
Data Retention Current	I_{CCDR1}	V_{CC} = 3V		1.0	mA

DATA RETENTION CHARACTERISTICS FOR L-VERSION

(T_A = -40°C to +85°C)

Parameter	Symbol	Conditions	Min	Max	Units
Data Retention Supply Voltage	V_{DR}	$\overline{CS_1}$ Controlled: $\overline{CS_1} \geq V_{CC}$ - 0.2V, $CS_2 \geq V_{CC}$ - 0.2V CS_2 Controlled: $CS_2 \leq$ 0.2V	2.0	5.5	V
Data Retention Current	I_{CCDR2}	V_{CC} = 3V		100	µA

AC CHARACTERISTICS

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter Read Cycle	Symbol	-17* Min	 Max	-20 Min	 Max	Units
Read Cycle Time	t_{RC}	17		20		nS
Address Access Time	t_{AA}		17		20	nS
Output Hold from Address Change	t_{OH}	2		2		nS
Chip Select Access Time	t_{ACS}		17		20	nS
Output Enable to Output Valid	t_{OE}		9		10	nS
Chip Select to Output in Low Z	t_{CLZ}[1]	3		3		nS
Output Enable to Output in Low Z	t_{OLZ}[1]	0		0		nS
Chip Disable to Output in High Z	t_{CHZ}[1]		10		12	nS
Output Disable to Output in High Z	t_{OHZ}[1]		8		9	nS

1.This parameter is guaranteed by design but not tested.
* Industrial temp only.

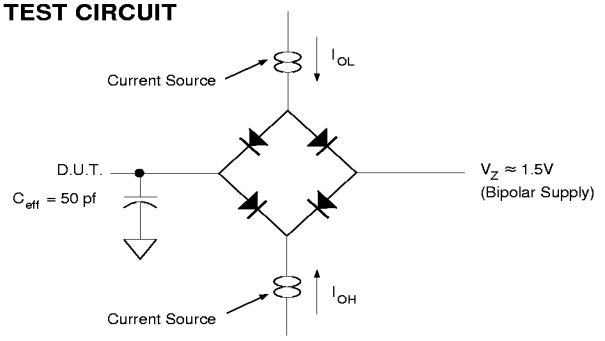
AC CHARACTERISTICS

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter Write Cycle	Symbol	-17* Min	 Max	-20 Min	 Max	Units
Write Cycle Time	t_{WC}	17		20		nS
Chip Select to End of Write	t_{CW}	14		17		nS
Address Valid to End of Write	t_{AW}	14		17		nS
Data Valid to End of Write	t_{DW}	11		12		nS
Write Pulse Width	t_{WP}	13		15		nS
Address Setup Time	t_{AS}	0		0		nS
Address Hold Time	t_{AH}	2		2		nS
Output Active from End of Write	t_{OW}[1]	0		0		nS
Write Enable to Output in High Z	t_{WHZ}[1]		8		10	nS
Data Hold Time	t_{DH}	0		0		nS

1.This parameter is guaranteed by design but not tested.
* Industrial temp only.

AC TEST CIRCUIT

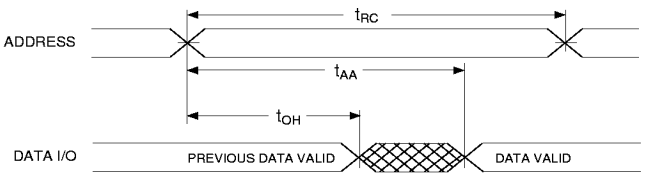


AC TEST CONDITIONS

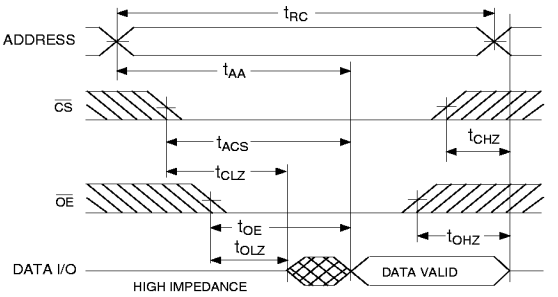
Parameter	Typ	Unit
Input Pulse Levels	V_{IL} = 0, V_{IH} = 3.0	V
Input Rise and Fall	5	nS
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

NOTES:
V_Z is programmable from -2V to +7V.
I_{OL} & I_{OH} programmable from 0 to 16mA.
Tester Impedance Z_0 = 75 Ω.
V_Z is typically the midpoint of V_{OH} and V_{OL}.
I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
ATE tester includes jig capacitance.

TIMING WAVEFORM - READ CYCLE

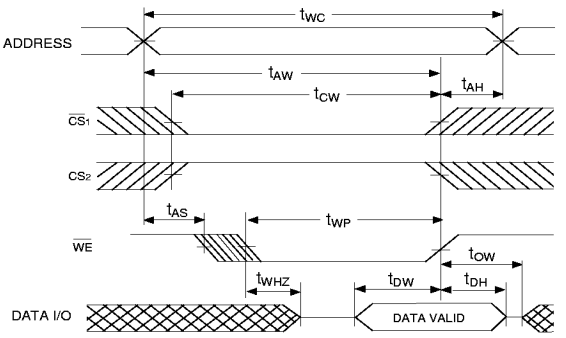


READ CYCLE 1 ($\overline{CS}$ = $\overline{OE}$ = V_{IL}, $\overline{WE}$ = V_{IH})



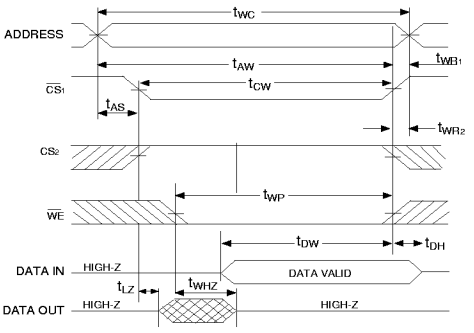
READ CYCLE 2 ($\overline{WE}$ = V_{IH})

WRITE CYCLE 1

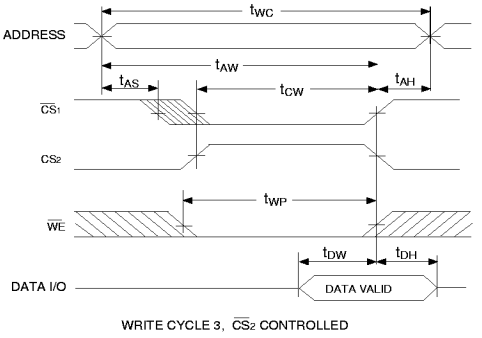


WRITE CYCLE 1 $\overline{WE}$ CONTROLLED

WRITE CYCLES 2 & 3

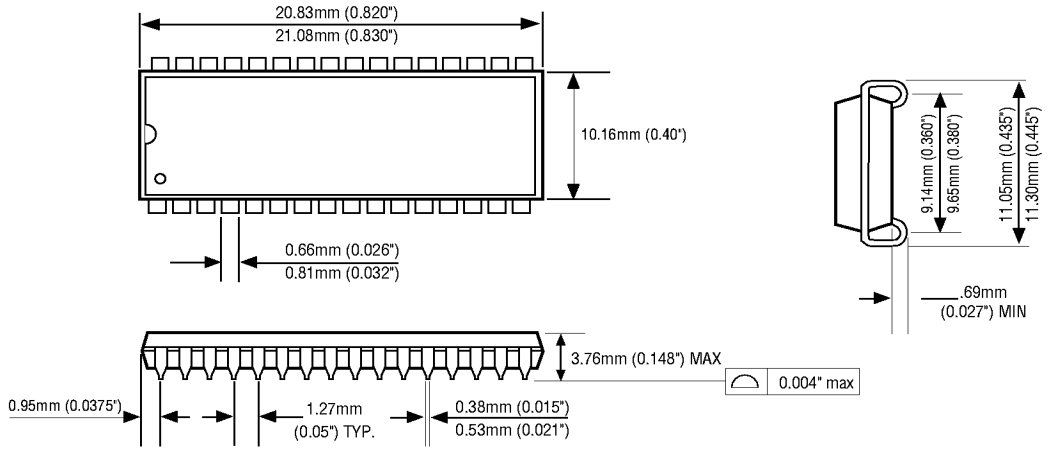


WRITE CYCLE 2, $\overline{CS_1}$ CONTROLLED



WRITE CYCLE 3, $\overline{CS_2}$ CONTROLLED

PACKAGE DIMENSION



ORDERING INFORMATION

W P S 128K 8 X X - XXX EJ X X

SPECIAL PROCESS:
Blank = CMOS

DEVICE GRADE:
M =Military Temperature -55°C to +125°C
I =Industrial Temperature -40°C to +85°C

PACKAGE:
EJ =Evolutionary SOJ

ACCESS TIME in nS

IMPROVEMENT MARK
B =Burn-in
T =Temperature Cycling
C =Burn-in and Temperature Cycle
L =Low Data Retention Current

ORGANIZATION, 128K x 8

SRAM

PLASTIC PLUS™

WHITE MICROELECTRONICS